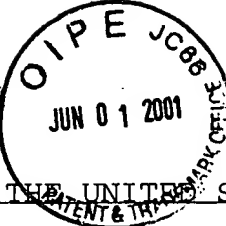


SON-1745



PATENT APPLICATION

1765

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of

Seiichi FUKUDA

Serial No. 09/512,336

Filed: February 24, 2000

For: DRY ETCHING METHOD AND
METHOD OF MANUFACTURING
SEMICONDUCTOR APPARATUS

Group Art Unit: 1765

Examiner: K. Chen

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COMMISSIONER FOR PATENTS
Washington, D.C. 20231

Sir:

Transmitted herewith is an amendment in the above-identified
application.

☒ No additional fee is required.

The fee has been calculated as shown below

CLAIMS AS AMENDED						
	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NO. PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE	ADDITIONAL FEE
TOTAL CLAIMS	8	MINUS	20	=0	x \$9 \$18	\$0.00
INDEP. CLAIMS	2	MINUS	3	=0	x\$40 \$80	\$0.00
Fee for Multiple Dependent Claims \$130/\$260						
			TOTAL ADDITIONAL FEE FOR THIS AMEND- MENT		\$0.00	

- If the entry in Column 2 is less than the entry in Column 4,
- write "0" in Column 5.
- ** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, write "20" in this space.
- *** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space.

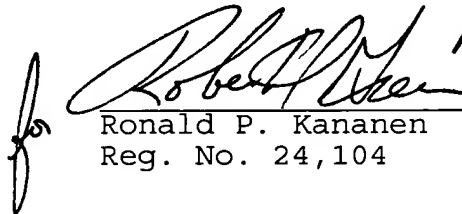


- ☐ A Letter to the Official Draftsperson is enclosed.
- ☐ A Change of Address is enclosed.
- ☐ Charge \$_____ to Deposit Account No. 18-0013. A duplicate copy of this sheet is enclosed.
- ☒ Any prior general authorization to charge an issue fee under 37 C.F.R. 1.18 to Deposit Account No. 18-0013 is hereby revoked. The Commissioner is hereby authorized to charge any additional fees under 37 CFR 1.16 and 1.17 which may be required during the entire pendency of this application, or to credit any overpayment, to Deposit Account No. 18-0013. A duplicate copy of this sheet is enclosed.
- ☐ Charge \$_____ to Deposit Account No. 18-0013 to cover the Extension fee for response within _____ month(s).
- ☒ Applicant's undersigned attorney may be reached by telephone in our Washington D.C. Office at

(202) 955-3750.

All correspondence should be directed to our below listed address.

Date: June 1, 2001


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AMENDMENT

Commissioner of Patents
Washington, DC 20231

Sir:

In response to the non-final Official Action mailed March 1, 2001 (Paper No. 4), please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims as shown in the Appendix. The claims as amended are presented immediately herebelow.

~~1. (amended) A dry etching method comprising the step of:
dry-etching tungsten with a mixed gas including a
fluorine-containing gas that includes a compound having
fluorine and carbon in a molecule, chlorine or hydrogen
bromide, oxygen, and nitrogen.~~

~~2. (amended) A dry etching method according to claim 1,
wherein said fluorine-containing gas has a structure that a
ratio of fluorine atoms with respect to elements of the gas
molecule except for fluorine is four or less when the
composition of the fluorine molecule is M_xF_y , $Y/X \leq 4$ where M
is an element except for fluorine atom and F is fluorine.~~